G03F

PHOTOMECHANICAL PRODUCTION OF TEXTURED OR PATTERNED SURFACES, e.g. FOR PRINTING, FOR PROCESSING OF SEMICONDUCTOR DEVICES; MATERIALS THEREFOR; ORIGINALS THEREFOR; APPARATUS SPECIALLY ADAPTED THEREFOR; (phototypographic composing devices B41B; photosensitive materials or processes for photographic purposes G03C; electrophotography, sensitive layers or processes therefor G03G)

Definition statement

This place covers:

Photolithographic materials, processing these materials for producing textured or patterned surfaces, and apparatus for processing these materials.

References

Limiting references

This place does not cover:

Phototypographic composing devices	<u>B41B</u>
Apparatus or arrangements for taking, projecting or viewing photographs	<u>G03B</u>
Photosensitive materials or processes for photographic purposes	<u>G03C</u>
Electrophotography, sensitive layers or processes thereof	<u>G03G</u>
Holographic processes and apparatus	<u>G03H</u>
Reproduction of pictures or patterns by scanning and converting into electrical signals	<u>H04N</u>

Special rules of classification

The following IPC groups are not used in the internal ECLA classification system. Subject-matter covered by these groups is classified in the following ECLA groups:

G03F3/08 covered by H04N 1/46

G03F7/207 " G03F 7/20

G03F7/23 " G03F 7/22

G03F9/02 " G03F 9/00

Glossary of terms

In this place, the following terms or expressions are used with the meaning indicated:

Photosensitive	Sensitive to electromagnetic radiation but also to corpuscular radiation
Photosensitive compositions	Photosensitive substances, e.g. quinonediazides, and, if applicable, binders or additives
Photosensitive materials	Photosensitive compositions, e.g. photoresists, the bases carrying them and, if applicable, auxiliary layers

G03F 1/00

Originals for photomechanical production of textured or patterned surfaces, e.g., masks, photo-masks, reticles; Mask blanks or pellicles therefor; Containers specially adapted therefor; Preparation thereof

Definition statement

This place covers:

Products modifying the pattern of radiation being transmitted through or reflected by said products (e.g. masks, photomasks, reticles), substrates therefor, auxiliary features (e.g. pellicles or auxiliary structures), process for their preparation, control and repair, containers for storage and/or transport of said products.

References

Limiting references

This place does not cover:

Masking layers which are integral part of a photosensitive element and photosensitive as such	G03F 7/095
Masking layers which are integral part of a photosensitive element provided they are not photosensitive as such	G03F 7/20
Addressable masks, e.g. transmissive liquid crystal arrays or micromirror devices	G03F 7/20, G02F 1/1335, G02B 26/08
Masks for photoablative processes	B23K 26/00
Deposition masks	C23C 14/00
Aperture plates for light beam shaping, e.g. diaphragms	<u>G03B</u> , <u>G02B</u>
Holographic devices to modify light pattern	G03H 1/00
Shadow mask for CRT	H01J 29/00
Shaping beams in charged particle lithography	H01J 37/317
Etch masks in semiconductor manufacturing	H01L 21/027

Informative references

Stencil masks	B41N 1/00, B24C 1/00, H01J 37/00
Transparent substrates	<u>C03B</u> , <u>C03C</u>
Phase plates (phase retarding optical elements)	G02B 5/00
Mirrors, particularly UV and EUV	G02B 5/00, G21K 1/00
Phase masks for gratings	G02B 6/02
Photographic masks, negatives	<u>G03C</u>
Mask or circuit layout	G06F 30/00
Inspection of patterns and materials	<u>G06T</u> , G02N
Membranes for X-Ray windows	H01J 33/00

Glossary of terms

In this place, the following terms or expressions are used with the meaning indicated:

Mask or photomask	Normally refers to 1:1 reproduction
Reticle	Normally involves (de)magnification - the terms mask and reticle are however often considered synonyms.
Pellicle	Protective cover placed at a distance from the surface of a reticle.
EUV (extreme ultraviolet)	Electromagnetic radiation in the 5-15 nm range (typically 13.4 nm)
SCALPEL	Scattering with angular limitation in projection electron beam lithography (characterized by the use of a membrane mask rather than a stencil mask)
PSM	Phase-shifting mask
AttPSM	Attenuated phase-shifting mask, aka half-tone PSM
AltPSM	Alternating phase-shifting mask, aka Levenson-Shibuya mask
Phase edge PSM	No absorber between phase shifting areas
OPC	Optical proximity correction
PPC	Process proximity correction

Synonyms and Keywords

In patent documents, the following words/expressions are often used as synonyms:

- "mask", "photomask", "reticle" and "reticule"
- "AttPSM", "Half-tone PSM" and "Leaky chrome PSM"
- "Grey level" and "Half-tone"

G03F 3/00

Colour separation; Correction of tonal value (photographic copying apparatus in general G03B)

Definition statement

This place covers:

Non numerical rendition of colours; non numerical colour proofing.

References

Limiting references

Producing decorative effects (e.g. by transfer pictures, decalcomanias, by pressing or stamping ornemental designs on surfaces)	B44C
General purpose image data processing (e.g. numerical colour conversion)	G06T 1/00
Numerical treatment of images	H04N 1/00

Informative references

Attention is drawn to the following places, which may be of interest for search:

Duplicating or marking methods; sheet materials for use therein	B41M 5/00
Photographic copying apparatus in general	<u>G03B</u>

G03F 5/00

Screening processes; Screens therefor {(plates or light sensitive layers with incorporated screen G03F 7/004)}

Definition statement

This place covers:

Creation of half-tone patterns from continuous tone images using photolithographic / photomechanical processes.

References

Limiting references

This place does not cover:

Plates or light sensitive layers with incorporated screen	G03F 7/004
Screen printers, printing screens and processes in general	B41F 15/00, G03F 7/12
Photolith films, i.e. high contrast AgX photographic materials	<u>G03C</u>
Digital treatment of continuous tone images in order to transform them into half-tone patterns	H04N 1/00

Informative references

Attention is drawn to the following places, which may be of interest for search:

Cameras	<u>G03B</u>
Image treatment	<u>G06T</u>

G03F 7/00

Photomechanical, e.g. photolithographic, production of textured or patterned surfaces, e.g. printing surfaces; Materials therefor, e.g. comprising photoresists; Apparatus specially adapted therefor (using photoresist structures for special production processes, see the relevant places, e.g. <u>B44C</u>, <u>H01L</u>, e.g. <u>H01L 21/00</u>, <u>H05K</u>)

Definition statement

This place covers:

Photolithographic production of textured or patterned surfaces, e.g. printing surfaces; materials therefor, e.g. comprising photoresists; apparatus specially adapted therefor (using photoresist structures for special production processes, see the relevant places, e.g. <u>B44C</u>, <u>H01L</u>, e.g. <u>H01L 21/00</u>, <u>H05K</u>); imprint lithography.

References

Limiting references

This place does not cover:

Structuring a surface by laser beam	B23K 26/00
Stereolithographic processes and apparatus	B29C
Printing plate preparation (e.g. by laser ingraving)	B41C 1/00
Duplicating or marking methods; Sheet materials for use therein (e.g. inkjet printing, ablative recording, thermography)	B41M 5/00
Preparing for use and conserving printing surfaces (e.g. chemical or electrical treatment of aluminum support)	B41N 3/00
Producing decorative effects (e.g. by transfer pictures, decalcomanias, by pressing or stamping ornemental designs on surfaces)	B44C
Investigating or analyzing materials by use of optical means (e.g. pattern inspection)	G01N 21/00
Apparatus for photographic purposes	<u>G03B</u>
Photosensitive materials for photographic purposes (mainly silver halide containing system)	<u>G03C</u>
Electrography, electrophotography, magnetography	<u>G03G</u>
Holographic processes and apparatus using light	G03H 1/00
General purpose image data processing (e.g. numerical colour conversion)	G06T 1/00
Lithographic apparatus using electron beam	H01J 37/00
Process or apparatus adapted for the manufacture or treatment of semiconductors (except for coating, exposure and development of photoresist)	H01L 21/00
Numerical treatment of images	H04N 1/00
Printed circuit boards	<u>H05K</u>

Informative references

Process for applying liquids	B05D 1/00
Lithographic printing form preparation using heat	B41C 1/00, B41M 5/00
Printing form preparation by laser ingraving	B41C 1/05
Infrared sensitive printing plate	B41C 1/10, B41M 5/40
Inkjet printers, thermal printers	<u>B41J</u>
Nanostructures	B82Y 30/00
Inorganic glasses	C03C 3/00
Polymerization processes using a photoinitiator system	C08F 2/50
Addition polymers or copolymers, ethylenic monomers	C08F 220/00
Condensation polymers of aldehydes or ketones with phenols only, e.g. novolak resins	C08G 8/00
Polystyrenes	C08L 25/06

Homopolymers or copolymers of compounds having one or more unsaturated aliphatic radicals, each having only one carbon-to-carbon double bond, and only one being terminated by only one carboxyl radical, or of salts, anhydrides, esters, amides, imides or nitriles thereof	C08L 33/00
Epoxide compounds, epoxy resins	C08L 63/00
Polyesters	C08L 67/00
Polyurethanes	C08L 75/04
Polyamides	C08L 77/00
Polyimides	C08L 79/08
Polysiloxanes	C08L 83/04
Organic dyes / pigments	<u>C09B</u>
Curable inks	C09D 11/10
Adhesives	<u>C09J</u>
Detergent compositions	C11D 1/00, C11D 3/00
Biological test and sensors	G01N 33/00
Optical fibres, mirrors, lenses	<u>G02B</u>
Colour filters (structures):	G02B 5/20
Liquid crystal display	G02F 1/00
Recording or reproducing by optical means, by modifying optical properties or the physical structure (holographic medium, optical disks, compact disks or CD, digital versatile disks or DVD)	G11B 7/00
Cathode ray tubes, electron or ion beam tubes	H01J 31/00, H01J 29/00

Glossary of terms

In this place, the following terms or expressions are used with the meaning indicated:

Photolithography	(1) Printing: Lithography in which the image is photographically transferred to the printing surface; esp. a planographic printing process using plates prepared from photographic negatives, usually printed by offset methods. (2) Electronics: A photoetching process in which a photomask is used in transferring the pattern to the photoresist, used esp. in the making of integrated circuits.
Radiation	Energy radiated in the form of electromagnetic waves or particles
Photoresist	Radiation-sensitive material, whose solubility is altered by exposure to radiation.
Negative-tone resist	The resist film beneath the clear areas of the photomask undergoes a chemical change that renders it insoluble in the developing solution.
Positive tone resist	The resist film beneath the clear areas of the photomask undergoes a chemical change that renders it soluble in the developing solution.
Imprint Lithography	A technique that creates patterns by mechanical deformation of imprint resist and subsequent processes.

Synonyms and Keywords

In patent documents, the following words/expressions are often used with the meaning indicated:

ARC	Antireflective coating
BARC	Bottom antireflective coating
CAR	Chemically amplified resist
DUV	Deep UV (248 nm)
EUV	Soft X-ray (13 nm)
Flexographic plate	Relief or intaglio printing plate
I-line	365 nm
LCD	Liquid crystal display
LIGA	Lithography Electroplating Molding
LER	Line edge roughness
Lithographic printing plate	Planographic printing plate or offset printing plate
PAG	Photoacid generator
PAC	Photoactive compound
PEB	Post exposure bake
Photomask	Optical mask
Relief Printing	Letterpress, flexography
Resin	Polymeric compound
Serigraphy	Screen printing

G03F 7/0002

{Lithographic processes using patterning methods other than those involving the exposure to radiation, e.g. by stamping}

Definition statement

This place covers:

Micro- and nanostructuring of surfaces based on transfer printing and imprinting processes, specially adapted as alternatives for photolithographic processes. It also includes use of cantilevers for depositing, mechanically removing or displacing material for the same purpose.

References

Limiting references

Patterning of substrates with cantilevers, based on electrically induced processes	G03F 7/20
Patternwise deposition of biomolecules	A61K 9/00, B01J, B01L/00
Handling of individual nanostructures, atoms or molecular structures using cantilevers	<u>B82B</u>
Embossing processes for optical data carriers (CD, DVD)	G11B 7/00
Cantilevers or micropoint sources in e-beam lithography	H01J 37/00

Informative references

Attention is drawn to the following places, which may be of interest for search:

Embossing in general	<u>B29C</u>
Printing processes for forming pattern structures of organic semiconductive material	H10K 71/13

Glossary of terms

In this place, the following terms or expressions are used with the meaning indicated:

SFIL	Step and Flash Imprint Lithography
NIL	Nanoimprint lithography
Dip-Pen nanolithography, aka DPN	Deposition from cantilever using fluid transfer

G03F 7/0007

{Filters, e.g. additive colour filters; Components for display devices}

Definition statement

This place covers:

Radiation-sensitive compositions for colour filters, black matrix, etc, and processes

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Colour filters (structures)	G02B 5/20
Liquid crystal displays	G02F 1/00

G03F 7/001

{Phase modulating patterns, e.g. refractive index patterns}

Definition statement

This place covers:

Radiation-sensitive compositions for holographic applications, and processes.

References

Limiting references

Holographic processes and apparatus using light	G03H 1/00
Recording or reproducing by optical means, by modifying optical properties or the physical structure (holographic medium, optical disks, compact disks or CD, digital versatile disks or DVD)	G11B 7/00

{Production of three-dimensional images}

Definition statement

This place covers:

Radiation-sensitive compositions for stereolithographic applications and processes.

G03F 7/004

Photosensitive materials (G03F 7/12, G03F 7/14 take precedence)

References

Limiting references

This place does not cover:

Production of screen printing forms or similar printing forms, e.g. stencils	G03F 7/12
Production of collotype printing forms	G03F 7/14

G03F 7/0041

{providing an etching agent upon exposure (G03F 7/075 takes precedence; photolytic halogen compounds G03F 7/0295)}

References

Limiting references

This place does not cover:

Photolytic halogen compounds	G03F 7/0295
Silicon-containing compounds	G03F 7/075

G03F 7/0042

{with inorganic or organometallic light-sensitive compounds not otherwise provided for, e.g. inorganic resists (G03F 7/075 takes precedence)}

References

Limiting references

Silicon-containing compounds	G03F 7/075

{Chalcogenides; Silicon, germanium, arsenic or derivatives thereof; Metals, oxides or alloys thereof (G03F 7/0044 takes precedence)}

Definition statement

This place covers:

e.g. use of metal alkoxide compounds (sol-gel technology) in photosensitive materials.

References

Limiting references

This place does not cover:

Organometallic compounds involving an interaction between the metallic	G03F 7/0044
and non-metallic component, e.g. photodope systems	

G03F 7/0045

{with organic non-macromolecular light-sensitive compounds not otherwise provided for, e.g. dissolution inhibitors}

Definition statement

This place covers:

Photoacid generating compounds, photobase generating compounds; acid diffusion inhibiting compounds (i.e. quencher).

References

Limiting references

This place does not cover:

Diazonium compounds	G03F 7/016, G03F 7/021
Diazoquinone compounds	G03F 7/022, G03F 7/023

G03F 7/0046

{with perfluoro compounds, e.g. for dry lithography (G03F 7/0048 takes precedence)}

Definition statement

This place covers:

Radiation-sensitive compositions containing fluorine-containing compounds in general

References

Limiting references

Photosensitive materials characterized by the solvents or agents	G03F 7/0048
facilitating spreading, e.g. surfactants	

{characterised by additives for obtaining a metallic or ceramic pattern, e.g. by firing}

Definition statement

This place covers:

Radiation-sensitive compositions containing inorganic microparticles as additives.

G03F 7/008

Azides (G03F 7/075 takes precedence)

References

Limiting references

This place does not cover:

Silicon-containing compounds	G03F 7/075
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G03F 7/012

Macromolecular azides; Macromolecular additives, e.g. binders {(G03F 7/0085 takes precedence)}

References

Limiting references

This place does not cover:

Non-macromolecular azides characterized by the non-macromolecular	G03F 7/0085
additives	

G03F 7/016

Diazonium salts or compounds (G03F 7/075 takes precedence)

References

Limiting references

Silicon-containing compounds	G03F 7/075
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Macromolecular diazonium compounds; Macromolecular additives, e.g. binders {(G03F 7/0166 takes precedence)}

References

Limiting references

This place does not cover:

Non-macromolecular diazonium salts characterised by the non-	G03F 7/0166
macromolecular additive	

G03F 7/022

Quinonediazides (G03F 7/075 takes precedence)

References

Limiting references

This place does not cover:

Silicon-containing compounds	<u>G03F 7/075</u>
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G03F 7/023

Macromolecular quinonediazides; Macromolecular additives, e.g. binders {(G03F 7/0226 takes precedence)}

References

Limiting references

This place does not cover:

Quinonediazides characterised by the non-macromolecular additives	G03F 7/0226

G03F 7/0236

{Condensation products of carbonyl compounds and phenolic compounds, e.g. novolak resins}

References

Informative references

Condensation polymers of aldehydes or ketones with phenols only, e.g.	C08G 8/00
novolak resins	

Non-macromolecular photopolymerisable compounds having carbon-to-carbon triple bonds, e.g. acetylenic compounds (G03F 7/075 takes precedence)

References

Limiting references

This place does not cover:

Silicon-containing compounds	<u>G03F 7/075</u>
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G03F 7/027

Non-macromolecular photopolymerisable compounds having carbon-to-carbon double bonds, e.g. ethylenic compounds (G03F 7/075 takes precedence)

Definition statement

This place covers:

Radiation-sensitive composition containing an addition polymerizable monomer having at least one ethylenically unsaturated double bond such as an acrylate or a methacrylate compound

References

Limiting references

This place does not cover:

Silicon-containing compounds	G03F 7/075
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Informative references

Attention is drawn to the following places, which may be of interest for search:

Macromolecular compounds obtained by reactions involving carbon-to	C08F 220/00
carbon unsaturated bonds	

G03F 7/029

Inorganic compounds; Onium compounds; Organic compounds having hetero atoms other than oxygen, nitrogen or sulfur

Definition statement

This place covers:

Inorganic photoinitiators or photosensitizers; Photoinitiators or photosensitizers containing other elements than carbon, hydrogen, oxygen, nitrogen and sulfur

References

Informative references

Polymerization processes using a photoinitiator system	C08F 2/50
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Organic compounds not covered by group G03F 7/029

Definition statement

This place covers:

Photoinitiators or photosensitizers containing the following elements only: carbon, hydrogen, oxygen, nitrogen and sulfur.

References

Limiting references

This place does not cover:

Organic compound having hetero atoms other than oxygen, nitrogen or	G03F 7/029
sulfur	

Informative references

Attention is drawn to the following places, which may be of interest for search:

Polymerization processes using a photoinitiator system	<u>C08F 2/50</u>	
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G03F 7/033

the binders being polymers obtained by reactions only involving carbon-tocarbon unsaturated bonds, e.g. vinyl polymers

Definition statement

This place covers:

Addition polymers as binders.

References

Informative references

Addition polymers or copolymers	C08F 220/00
Polystyrenes	C08L 25/06
Compositions of homopolymers or copolymers of compounds having one or more unsaturated aliphatic radicals, each having only one carbon-to-carbon double bond, and only one being terminated by only one carboxyl radical, or of salts, anhydrides, esters, amides, imides or nitriles thereof	C08L 33/00

the binders being polyurethanes

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

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Polyurethanes	C08L 75/04

G03F 7/037

the binders being polyamides or polyimides

Definition statement

This place covers:

e.g. polyamic acid, polybenzoxazoles, etc.

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Polyamides	C08L 77/00
Polyimides	C08L 79/08

G03F 7/038

Macromolecular compounds which are rendered insoluble or differentially wettable (G03F 7/075 takes precedence; macromolecular azides G03F 7/012; macromolecular diazonium compounds G03F 7/021)

Definition statement

This place covers:

Macromolecular photopolymerizable compounds; Non-macromolecular crosslinkable epoxy compounds are also classified in this subgroup.

References

Limiting references

Macromolecular azide compounds	G03F 7/012
Macromolecular diazonium compounds	G03F 7/021
The macromolecular compound being present in a chemically amplified negative photoresist composition	G03F 7/0382
Epoxidized novolak resins	G03F 7/0385
Silicon-containing compounds	G03F 7/075

Informative references

Attention is drawn to the following places, which may be of interest for search:

Epoxide compounds, epoxy resins	C08L 63/00
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G03F 7/0385

{using epoxidised novolak resin}

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Epoxy resins	C08L 63/00
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G03F 7/0387

{Polyamides or polyimides}

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Polyamides	C08L 77/00
Polyimides	C08L 79/08

G03F 7/039

Macromolecular compounds which are photodegradable, e.g. positive electron resists (G03F 7/075 takes precedence; macromolecular quinonediazides G03F 7/023)

Definition statement

This place covers:

Macromolecular and non-macromolecular photodegradable compounds.

References

Limiting references

Macromolecular quinonediazides	G03F 7/023
The macromolecular compound being present in a chemically amplified positive photoresist composition	G03F 7/0392
Silicon-containing compounds	G03F 7/075

Chromates (G03F 7/075 takes precedence)

References

Limiting references

This place does not cover:

Silicon-containing compounds	<u>G03F 7/075</u>
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G03F 7/06

Silver salts (G03F 7/075 takes precedence)

References

Limiting references

This place does not cover:

Silicon-containing compounds	<u>G03F 7/075</u>
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G03F 7/07

used for diffusion transfer {(G03F 7/063 takes precedence)}

References

Limiting references

This place does not cover:

Additives in silver salts systems; additives or means to improve the	G03F 7/063
lithographic properties; processing solutions characterised by such	
additives; treatment after development or transfer, e.g. finishing, washing;	
correction or deletion fluids	

G03F 7/0754

{Non-macromolecular compounds containing silicon-to-silicon bonds (G03F 7/0752 takes precedence)}

Definition statement

This place covers:

Macromolecular compounds containing silicon-to-silicon bonds are also classified in this subgroup.

References

Limiting references

Ì	Silicon-containing compounds in non photosensitive layers or as additives	G03F 7/0752
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{Non-macromolecular compounds containing Si-O, Si-C or Si-N bonds (G03F 7/0752 takes precedence)

References

Limiting references

This place does not cover:

Silicon-containing compounds in non photosensitive layers or as additives G03F 7/0752

G03F 7/0757

{Macromolecular compounds containing Si-O, Si-C or Si-N bonds (G03F 7/0752 takes precedence)}

Definition statement

This place covers:

Polymerized siloxanes or polysiloxanes (silicones), polysilazanes, etc.

References

Limiting references

This place does not cover:

Silicon-containing compounds in non photosensitive layers or as additives

G03F 7/0752

Informative references

Attention is drawn to the following places, which may be of interest for search:

Polysiloxanes	COOL	83/04
Polysiloxaries	ICUOL	. os/u4

G03F 7/085

Photosensitive compositions characterised by adhesion-promoting nonmacromolecular additives (G03F 7/075 takes precedence)

Definition statement

This place covers:

Adhesion-promoting macromolecular additives are also classified in this subgroup

References

Limiting references

Silicon-containing compounds used as adhesion-promoting additives	G03F 7/0751
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characterised by structural details, e.g. supports, auxiliary layers (supports for printing plates in general B41N)

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Supports for printing plates in general	<u>B41N</u>

G03F 7/091

{characterised by antireflection means or light filtering or absorbing means, e.g. anti-halation, contrast enhancement}

Definition statement

This place covers:

Antireflective compositions for bottom antireflective coating, top antireflective coating, etc.

G03F 7/095

having more than one photosensitive layer (G03F 7/075 takes precedence)

Definition statement

This place covers:

Versatile radiation-sensitive compositions (i.e. positive-negative tone) are also classified in this subgroup.

References

Limiting references

This place does not cover:

Photosensitive layers containing silicon-containing compounds	G03F 7/075

G03F 7/11

having cover layers or intermediate layers, e.g. subbing layers {(G03F 7/091 - G03F 7/093, B41N 3/03 take precedence)}

References

Limiting references

Antireflective coatings	G03F 7/091
Electroconductive coatings	G03F 7/093
Preparing for use and conserving printing surfaces	B41N 3/03

Coating processes; Apparatus therefor (applying coatings to base materials in general <u>B05</u>; applying photosensitive compositions to base for photographic purposes <u>G03C 1/74</u>)

Definition statement

This place covers:

Processes for coating a substrate. Specific treatments of the substrate before coating are also classified in this subgroup.

References

Limiting references

This place does not cover:

Applying coatings to base materials in general	<u>B05D</u>
Preparing for use and conserving printing surfaces	B41N 3/00
Applying photosensitive compositions to base for photographic purposes	G03C 1/74

G03F 7/167

(from the gas phase, by plasma deposition (G03F 7/2035 takes precedence)

References

Limiting references

This place does not cover:

Simultaneous coating and exposure	G03F 7/2035

G03F 7/168

{Finishing the coated layer, e.g. drying, baking, soaking}

Definition statement

This place covers:

Edge bead removal is also classified in this subgroup.

G03F 7/20

Exposure; Apparatus therefor (photographic printing apparatus for making copies G03B 27/00)

References

Limiting references

Photographic printing apparatus for making copies	G03B 27/00
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{in the presence of a fluid, e.g. immersion; using fluid cooling means}

Definition statement

This place covers:

Radiation-sensitive composition for immersion lithography, fluids used in immersion lithography.

G03F 7/2049

{using a cantilever}

Definition statement

This place covers:

e.g. Atomic force microscopy, scanning tunnel exposure techniques.

G03F 7/2051

{Exposure without an original mask, e.g. using a programmed deflection of a point source, by scanning, by drawing with a light beam, using an addressed light or corpuscular source (G03F 7/70 takes precedence)}

References

Limiting references

This place does not cover:

Apparatus for microlithography	G03F 7/70
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G03F 7/2053

{using a laser (ablative removal B41C)}

Definition statement

This place covers:

Multiphoton lithography is classified in this subgroup

References

Limiting references

Ablative removal of materials	<u>B41C</u>
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Exposing with the same light pattern different positions of the same surface at the same time {(G03F 7/70 takes precedence)}

References

Limiting references

This place does not cover:

Apparatus for microlithography	G03F 7/70
77 - 3 - 7 - 7 - 7 - 7 - 7 - 7 - 7 - 7 -	

G03F 7/22

Exposing sequentially with the same light pattern different positions of the same surface {(G03F 7/70 takes precedence)}

References

Limiting references

This place does not cover:

Apparatus for microlithography	<u>G03F 7/70</u>
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G03F 7/24

Curved surfaces {(G03F 7/70 takes precedence)}

References

Limiting references

This place does not cover:

Apparatus for microlithography	<u>G03F 7/70</u>
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G03F 7/26

Processing photosensitive materials; Apparatus therefor (G03F 7/12 - G03F 7/24 take precedence)

Definition statement

This place covers:

Various techniques of purification of radiation-sensitive materials are also classified in this subgroup.

References

Limiting references

Coating processes, apparatus thereof	G03F 7/16
Exposure, apparatus thereof	G03F 7/20 - G03F 7/24

{Selective reaction with inorganic or organometallic reagents after image-wise exposure, e.g. silylation}

Definition statement

This place covers:

Selective reaction with a reagent taking place before development. Selective reactions with organic reagents are also classified in this subgroup.

G03F 7/28

for obtaining powder images (G03F 3/10 takes precedence)

References

Limiting references

This place does not cover:

Checking the colour or tonal value of separation negatives or positives	,
using tonable photoresist or photopolymerizable systems	

G03F 3/103

G03F 7/3035

{from printing plates fixed on a cylinder or on a curved surface; from printing cylinders}

Definition statement

This place covers:

On press development is also included in this subgroup.

G03F 7/32

Liquid compositions therefor, e.g. developers

References

Limiting references

This place does not cover:

Gumming or finishing so	lutions for printing plates
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B41N 3/08

G03F 7/36

Imagewise removal not covered by groups <u>G03F 7/30</u> - <u>G03F 7/34</u>, e.g. using gas streams, using plasma

Definition statement

This place covers:

e.g. thermal development, development using gas streams, using plasma, photoembossing.

References

Limiting references

This place does not cover:

Imagewise removal using liquid means	G03F 7/30
Imagewise removal by selective transfer, e.g. peeling away	G03F 7/34
Etching (semiconductor technology)	H01L 21/00

G03F 7/38

Treatment before imagewise removal, e.g. prebaking {(G03F 7/265 takes precedence)}

Definition statement

This place covers:

Treatments such as post exposure bake

References

Limiting references

This place does not cover:

Selective reaction with organic, inorganic or organometallic reagents	G03F 7/265
before imagewise removal	

G03F 7/40

Treatment after imagewise removal, e.g. baking

Definition statement

This place covers:

Treatments such as post-development bake, thermal flow, pattern profile improvement.

G03F 7/405

{Treatment with inorganic or organometallic reagents after imagewise removal}

Definition statement

This place covers:

Treatments with organic reagents after imagewise removal are also classified in this subgroup.

G03F 7/42

Stripping or agents therefor

Definition statement

This place covers:

Stripping involving the use of a combination of means, e.g. plasma and radiation.

{using liquids only (G03F 7/421 takes precedence)}

References

Limiting references

This place does not cover:

Using biological means only, e.g. enzymes	G03F 7/421
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Informative references

Attention is drawn to the following places, which may be of interest for search:

Detergent compositions	C11D 1/00, C11D 3/00
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G03F 7/423

{containing mineral acids or salts thereof, containing mineral oxidizing substances, e.g. peroxy compounds}

Definition statement

This place covers:

Stripping agents containing organic oxidizing substances are also classified in this subgroup.

G03F 7/426

{containing organic halogen compounds; containing organic sulfonic acids or salts thereof; containing sulfoxides}

Definition statement

This place covers:

Stripping agents containing carboxylic acids or salts thereof are also classified in this subgroup.

G03F 7/427

{using plasma means only}

Definition statement

This place covers:

Stripping treatments using plasma, gas or supercritical fluids.

G03F 9/00

Registration or positioning of originals, masks, frames, photographic sheets or textured or patterned surfaces, e.g. automatically (G03F 7/22 takes precedence; preparation of photographic masks G03F 1/00; within photographic printing apparatus for making copies G03B 27/00)

Definition statement

This place covers:

Positioning and alignment of originals, i.e. mask or reticle with the target substrate to be exposed by actinic radiation. Positioning and alignment of a radiation beam with respect to the target in direct-write lithographic processes. Alignment marks on mask and target. Devices for carrying out the positioning and alignment.

References

Limiting references

This place does not cover:

Positioning in the preparation of photographic masks	G03F 1/00
Positioning in exposing sequentially with the same light pattern different positions of the same surface	G03F 7/22
Positioning of printing elements	<u>B41F</u> , <u>B41N</u>
Positioning within photographic printing apparatus for making copies	G03B 27/00
Positioning ion beams for patterning purposes	H01J 37/00
Overlay of successive layers in a multilayer patterned semiconductor or solid state device	H01L

Informative references

Attention is drawn to the following places, which may be of interest for search:

Detection of the position of an object on a substrate	<u>G01B</u>
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G03F 9/70

{for microlithography (measuring printed patterns for monitoring overlay G03F 7/70633 or focus G03F 7/70641; projection system adjustment G03F 7/70258; position control G03F 7/70775)}

Definition statement

This place covers:

Aligning an original with a workpiece in a lithographic apparatus. Alignment marks for originals or workpieces. Devices for carrying out the aligning.

References

Limiting references

This place does not cover:

Illumination system adjustment, alignment during assembly of illumination system and regular adjustment	G03F7/20T14
Beam registration in direct write photolithography	G03F7/20T18
Projection system adjustment, alignment during assembly of projection system and regular adjustment	G03F 7/70258
Measuring printed patterns for overlay control	G03F 7/70633
Measuring printed patterns for focus control	G03F 7/70641
Positioning device and position control in a lithographic apparatus	G03F 7/70775
Alignment of original or workpiece in charged particle beam lithography	H01J37/317B27

Informative references

Attention is drawn to the following places, which may be of interest for search:

Photomasks	G03F 1/00
Alignment marks specific to photomasks	G03F 1/62
Lithographic processes using patterning methods other than those involving exposure to radiation, e.g. by imprinting or transfer printing	G03F 7/0002
Apparatus for microlithography	G03F 7/70

Glossary of terms

In this place, the following terms or expressions are used with the meaning indicated:

Lithography	micro- and nanoprojection, proximity or contact photolithography; micro- and nanoimprint or transfer printing lithography
Original	e.g. reticle, photomask, addressable mask, imprint mold, stamp
Workpiece	target substrate to be patterned via lithography
Aligning	includes aligning in the substrate plane (i.e. aligning as such) and perpendicularly to the substrate plane (i.e. focussing or gap setting)